TECHNICAL DATA
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Diode Array

- ***Devices Are Serialized***
- ***Eight sets of double diodes in a single package***
- ***Die manufactured on qualified JANS line***
- ***Built and screened to space level quality (SDA1009SS)***
- ***Quality Conformance Inspection (QCI) in accordance with MIL-PRF-38534 is performed on each lot (SDA1009SS)***
- ***Add suffix "S" for screening per MIL-PRF-38534, Class H (SDA1009S)***
- ***Add suffix "SS" for Space Level Screening per MIL-PRF-38534, Class K (SDA1009SS)***
- ***Each diode similar to JANS1N5615***

MAX. RATINGS / ELECTRICAL CHARACTERISTICS FOR EACH DIODE

All rating at are $T_A = 25^oC$ unless otherwise specified

RATING	SYMBOL	MAX	UNIT
Peak Inverse Voltage (DC)	PIV	400	V
Average DC Output Current Per Diode $T_A = 55^oC$ $T_A = 100^oC$	I_O	1 0.75	A
Peak Single Cycle Surge Current (1) (T_P=8.3ms single half-Sine wave)	I_{FSM}	10	A
Steady State Power Dissipation per Package (2)	P_T	1000	mW
Max. Operating Junction Temperature	T_J	-55 to +150	^oC
Max. Operating Ambient Temperature	T_{OP}	-30 to 100	^oC
Storage Temperature Range	T_{STG}	-65 to +175	^oC
Maximum forward voltage @ 3.0A Tp = 300µs; 2% duty cycle	V_f	3.2	V
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^oC$ $T_A = 100^oC$	0.5 25	µA
Max. Reverse Recovery Time I_F =0.5 A, I_R= 1.0A, I_{RR} =0.25A	t_{rr}	150	ns
Max. Capacitance f= 1MHz, V_R = 12V	C_T	30	pF
Thermal Resistance Junction to Case	θ_{JC}	21	$^oC/W$

Note: (1) Each diode
(2) Derate at $8mW/^0C$ above 25^0C

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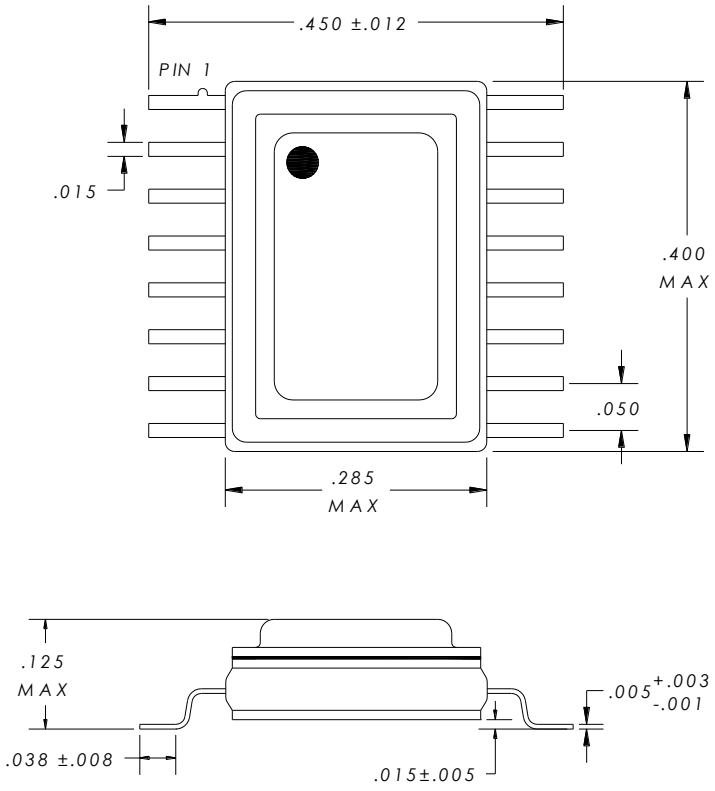
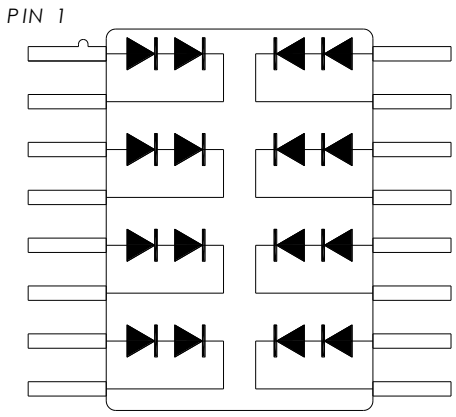
Mechanical Outline





Electrical Schematic